

Silicon N Channel MOS FET

REJ03G0978-0400 Rev.4.00 Jun 04, 2008

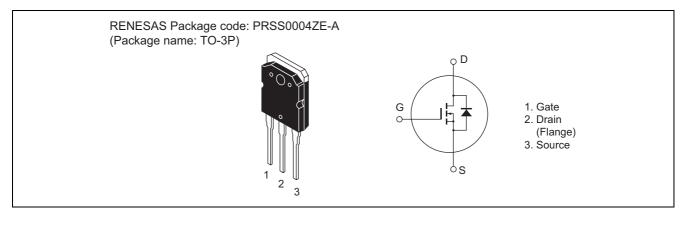
Application

High speed power switching

Features

- High breakdown voltage ($V_{DSS} = 1500 \text{ V}$)
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator

Outline



A 新动性的 Maxim供应 Batings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	1500	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	Ι _D	4	A
Drain peak current	I _{D(pulse)} Note1	10	A
Body to drain diode reverse drain current	I _{DR}	4	A
Channel dissipation	Pch Note2	125	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1 %

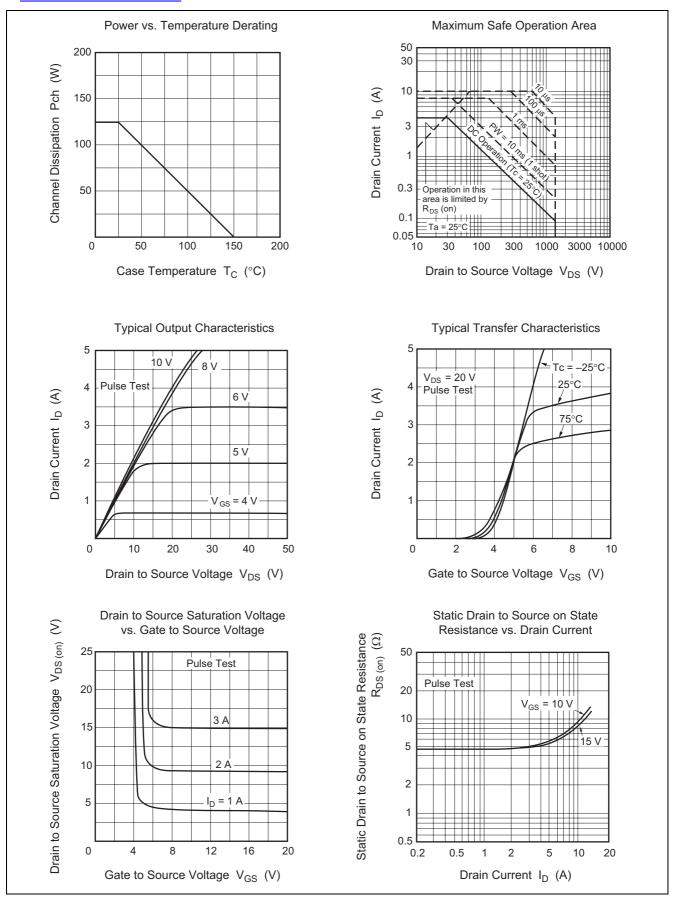
2. Value at $Tc = 25^{\circ}C$

Electrical Characteristics

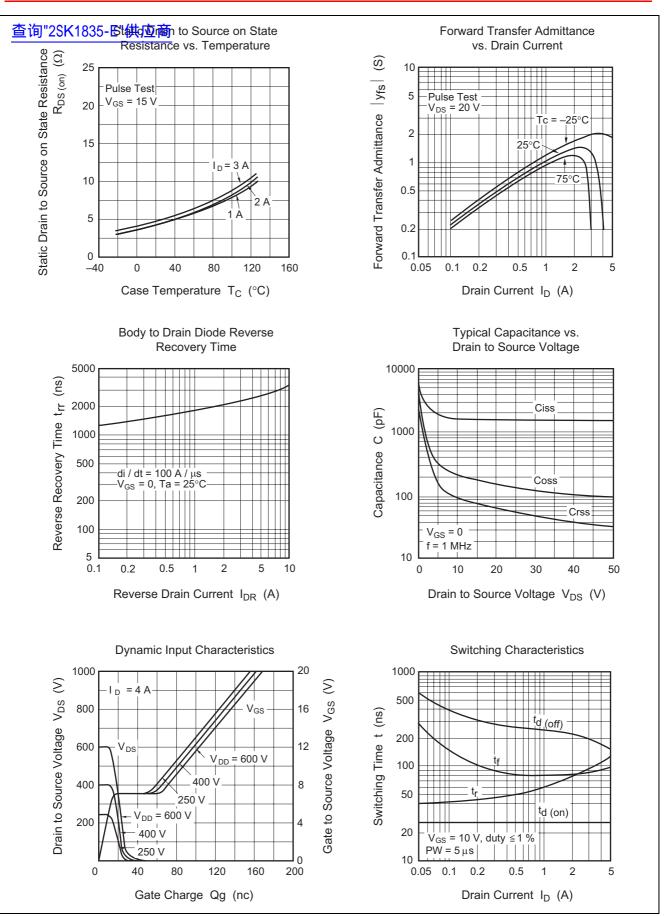
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	1500	—	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	—	±1	μΑ	$V_{GS} = \pm 20 V, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	—	500	μΑ	$V_{DS} = 1200 \text{ V}, \text{ V}_{GS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	2.0	—	4.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	R _{DS(on)}	_	4.6	7.0	Ω	$I_D = 2 \text{ A}, V_{GS} = 15 \text{ V}^{Note 3}$
Forward transfer admittance	y _{fs}	0.9	1.4	_	S	$I_D = 2 \text{ A}, V_{DS} = 20 \text{ V}^{\text{Note 3}}$
Input capacitance	Ciss	—	1700	—	pF	$V_{DS} = 10 V, V_{GS} = 0,$
Output capacitance	Coss	—	230	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	—	100	—	pF	
Turn-on delay time	t _{d(on)}	—	25	_	ns	$I_D = 2A, V_{GS} = 10 V,$
Rise time	tr	—	80	_	ns	R _L = 15 Ω
Turn-off delay time	t _{d(off)}	—	230	_	ns	
Fall time	t _f	_	80	_	ns	
Body to drain diode forward voltage	V _{DF}	_	0.85		V	$I_F = 4 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t _{rr}	_	2500	—	ns	I _F = 4 A, V _{GS} = 0, di _F /dt = 100 A/μs

Note: 3. Pulse Test

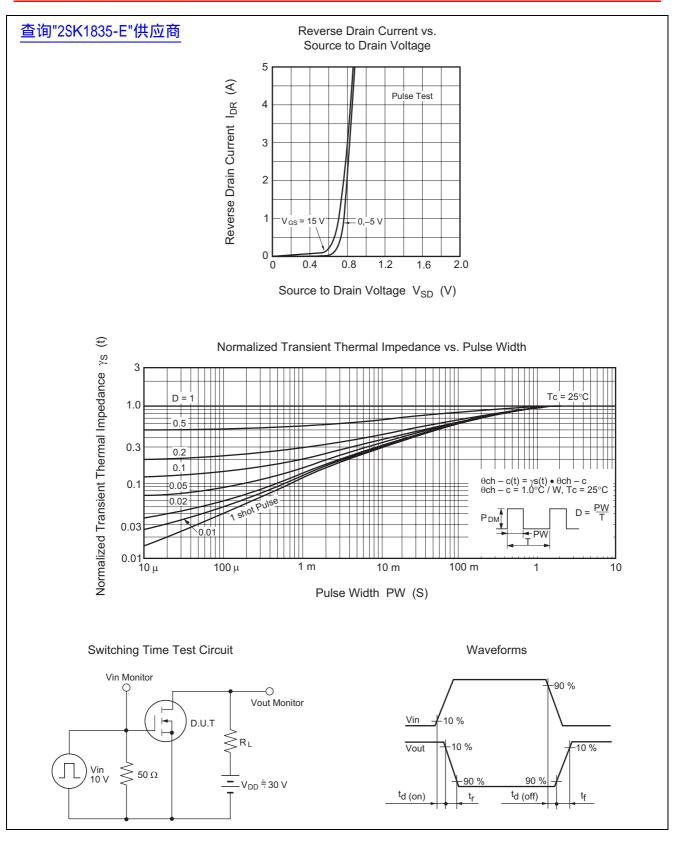
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Package Dimensions

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]	
TO-3P	SC-65	PRSS0004ZE-A	TO-3P / TO-3PV	5.0g	Unit: mm
	<u>1.6</u> <u>1.4 Ma</u>	15.6 ± 0.3	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	4.8 ± 0.2 1.5 0.6 ± 0.2	
	<u>5.45 ± 0</u>		<u>2</u> .0 <u>1</u> <u>5.45 ± 0.5</u>		

Ordering Information

Part Name	Quantity	Shipping Container
2SK1835-E	360 pcs	Box (Tube)

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